

General Description

The WST3400A is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the small power switching and load switch applications.

The WST3400A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

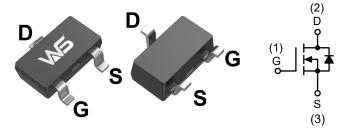
Product Summery

BV _{DSS}	R _{DSON}	I _D	
30V	20mΩ	6.4A	

Applications

- High Frequency Point-of-Load Synchronous s Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

		Ra	ting	
Symbol	Parameter	10s	Steady State	Units
V _{DS}	Drain-Source Voltage	3	V	
V_{GS}	Gate-Source Voltage		12	V
I _D @T _c =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	7.7	6.4	Α
I _D @T _c =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	6.2	5.4	Α
I _{DM}	Pulsed Drain Current ²	2	23	Α
P _D @T _A =25℃	Total Power Dissipation ³	1.32	1	W
P _D @T _A =70°C	Total Power Dissipation ³	0.84	0.64	W
T _{STG}	Storage Temperature Range	-55 t	o 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 t	o 150	$^{\circ}$

Thermal Data

Symbol	Symbol Parameter		Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-ambient ¹		125	°C/W
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤10s)		95	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		80	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.025		V/°C	
В	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =5A		20	31	m0	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =2.5V , I _D =4A		28	46	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	V =V 1 =250A	0.5	0.8	1.2	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$-V_{GS}=V_{DS}$, $I_D=250uA$		-4.8		mV/℃	
	Drain Source Leekage Current	V_{DS} =24V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	uA	
I _{DSS}	Drain-Source Leakage Current	V_{DS} =24V , V_{GS} =0V , T_J =55 $^{\circ}$ C			5		
I _{GSS}	Gate-Source Leakage Current	V_{GS} = \pm 12 V , V_{DS} =0 V			±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =5A		7		S	
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.5	5	Ω	
Qg	Total Gate Charge (4.5V)			5.8	8.4		
Q_{gs}	Gate-Source Charge	V_{DS} =15V , V_{GS} =4.5V , I_{D} =5A		2.4	3.5	nC	
Q_gd	Gate-Drain Charge			2.0	2.9		
$T_{d(on)}$	Turn-On Delay Time			2.3	4.8		
T _r	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω		7.6	14	20	
T _{d(off)}	Turn-Off Delay Time	I _D =5A		3.8	8	ns	
T _f	Fall Time			21	44		
C _{iss}	Input Capacitance			520	880		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		72	112	pF	
C _{rss}	Reverse Transfer Capacitance			56	91		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,4})/ -\/ -0\/ Force Correct			1.8	Α
I _{SM}	Pulsed Source Current ^{2,4}	$V_G=V_D=0V$, Force Current			22	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25℃			1.2	V
t _{rr}	Reverse Recovery Time			18		nS
Q _{rr}	Reverse Recovery Charge	IF=5A , dI/dt=100A/ μ s , T $_{J}$ =25 $^{\circ}$ C		3		nC

Note

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10 sec.
- 2.The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$
- 3. The power dissipation is limited by 150 ℃ junction temperature
- 4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



N-Ch MOSFET

Typical Characteristics

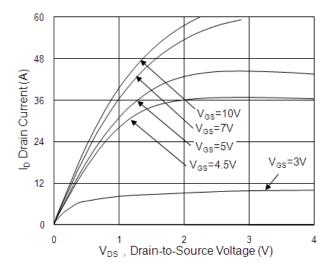


Fig.1 Typical Output Characteristics

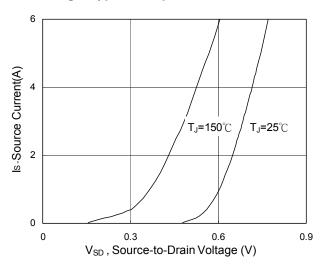


Fig.3 Forward Characteristics Of Reverse

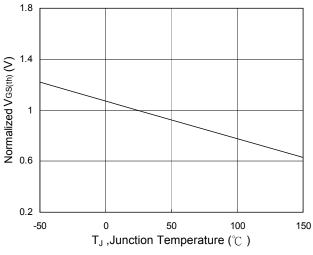


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

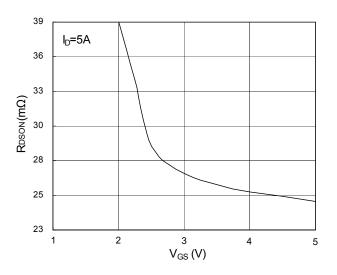


Fig.2 On-Resistance vs. Gate-Source

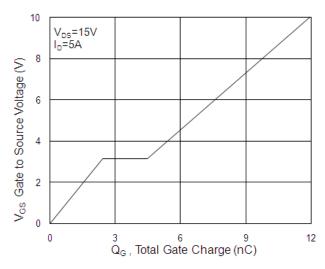


Fig.4 Gate-Charge Characteristics

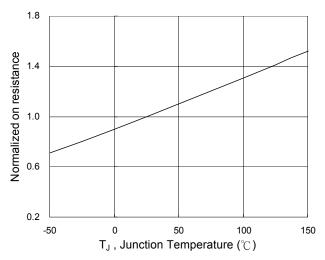
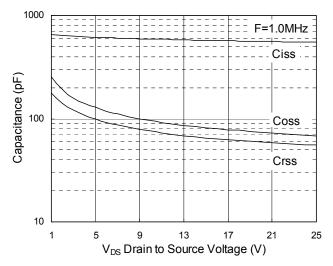


Fig.6 Normalized R_{DSON} vs. T_J





100.00

10.00

10.00

10.00

100ms

Fig.7 Capacitance

Fig.8 Safe Operating Area

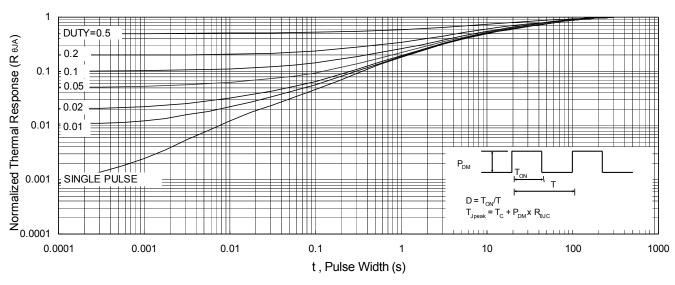
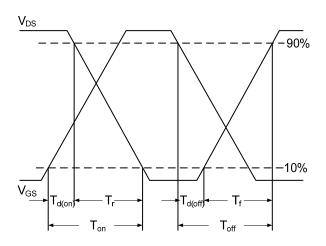


Fig.9 Normalized Maximum Transient Thermal Impedance



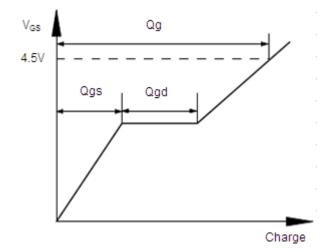
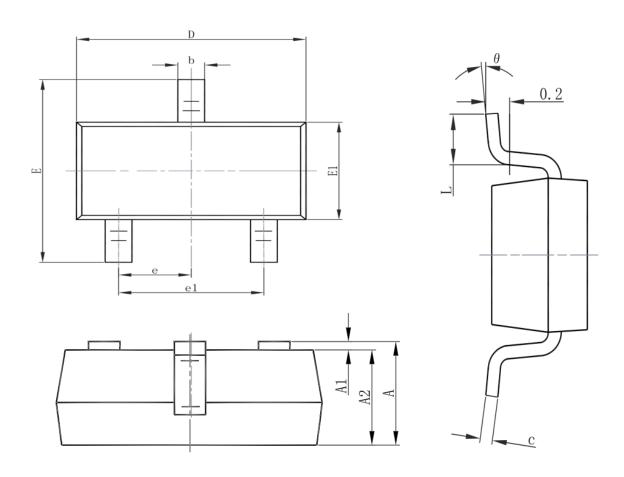


Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform



Packaging information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches	
	Min.	Max.	Min.	Max.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
Е	2.650	2.950	0.104	0.116
е	0.950	(BSC)	0.037(BSC)	
e1	1.800	2.000	0.071 0.	
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°



Attention

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5,In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.
- 9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.